



<b>THERMAL AND MECHANICAL SPECIFICATIONS</b>					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Junction to case IGBT	$R_{thJC}$ (IGBT)	-	-	0.38	°C/W
Junction to case DIODE	$R_{thJC}$ (DIODE)	-	-	1.00	
Case to sink, flat, greased surface	$R_{thCS}$ (MODULE)	-	0.05	-	
Mounting torque (M5)		2.7	-	3.3	Nm
Weight		-	170	-	g

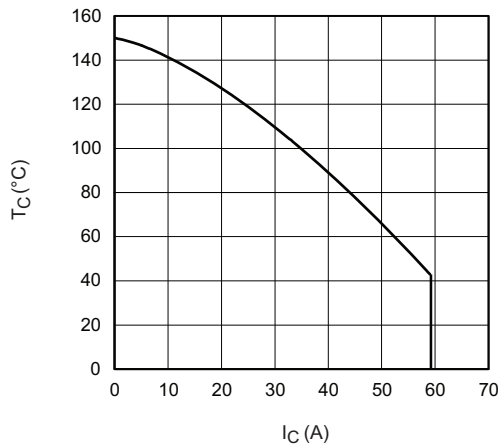


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

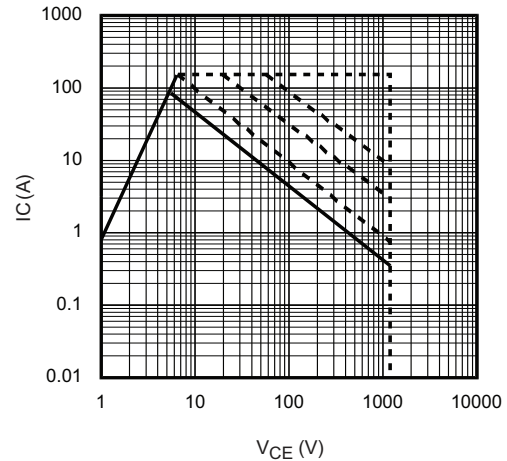


Fig. 3 - Forward SOA  
 $T_C = 25\text{ }^\circ\text{C}$ ;  $T_J \leq 150\text{ }^\circ\text{C}$

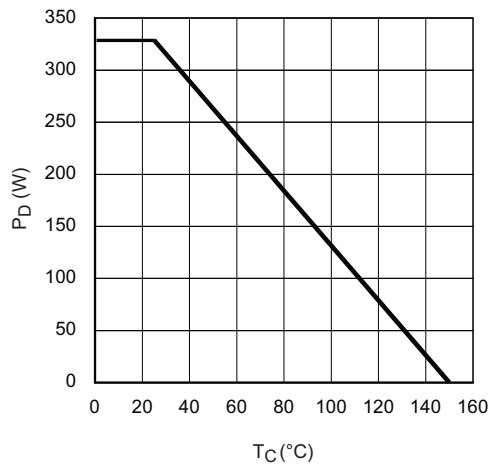


Fig. 2 - Power Dissipation vs. Case Temperature

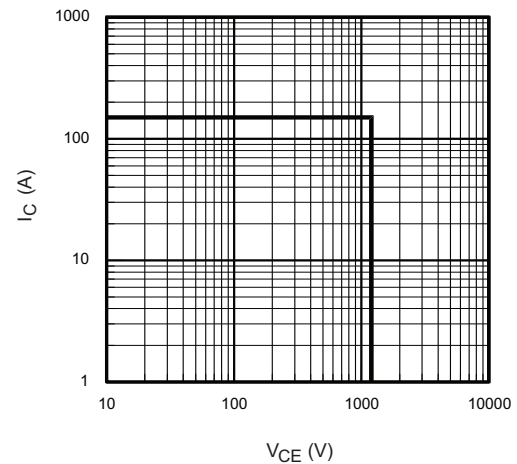


Fig. 4 - Reverse Bias SOA  
 $T_J = 150\text{ }^\circ\text{C}$ ;  $V_{GE} = 15\text{ V}$

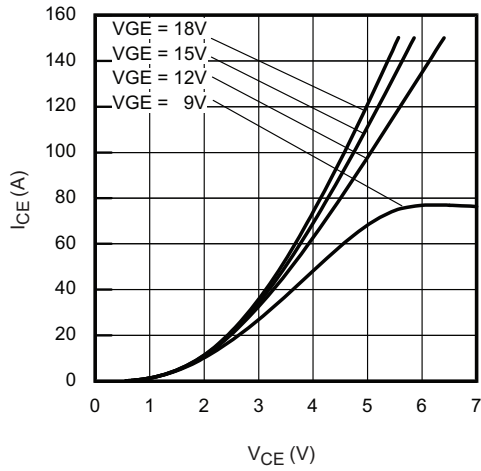


Fig. 5 - Typical IGBT Output Characteristics  
 $T_J = 25\text{ }^\circ\text{C}$ ;  $t_p = 500\text{ }\mu\text{s}$

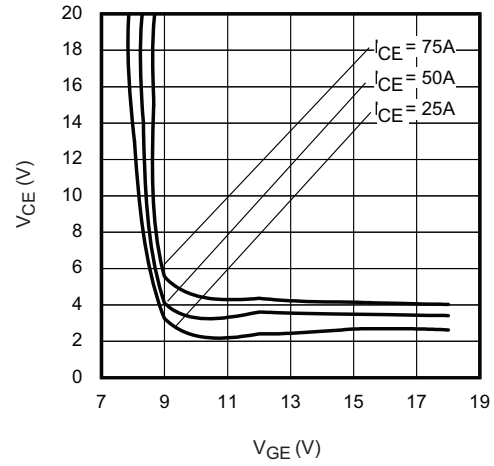


Fig. 8 - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 25\text{ }^\circ\text{C}$

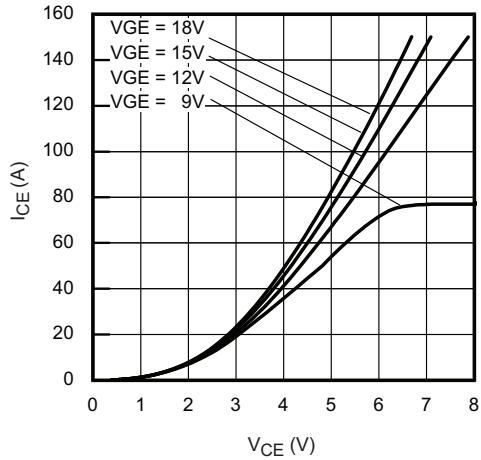


Fig. 6 - Typical IGBT Output Characteristics  
 $T_J = 125\text{ }^\circ\text{C}$ ;  $t_p = 500\text{ }\mu\text{s}$

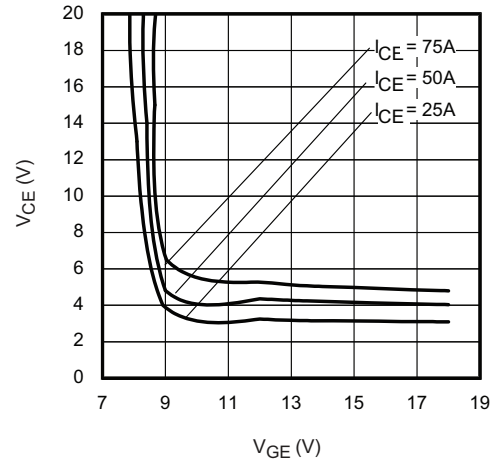


Fig. 9 - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 125\text{ }^\circ\text{C}$

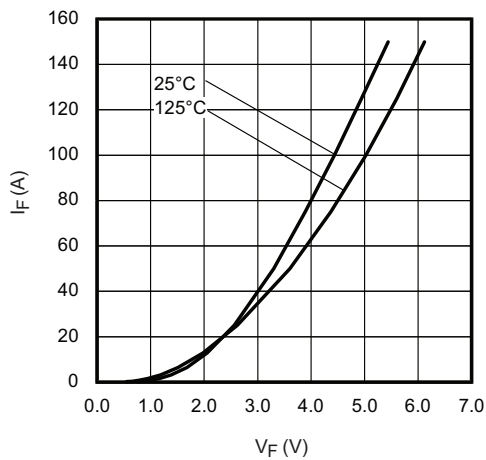


Fig. 7 - Typical Diode Forward Characteristics  
 $t_p = 500\text{ }\mu\text{s}$

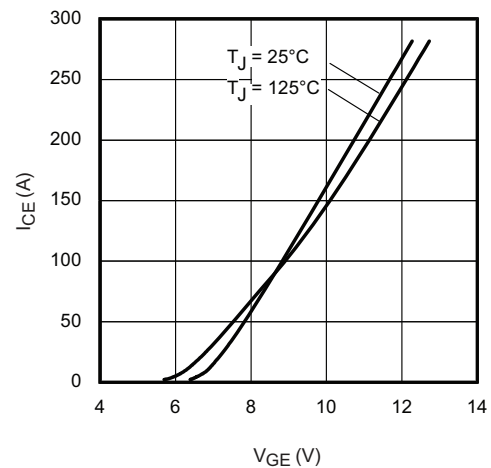


Fig. 10 - Typical Transfer Characteristics  
 $V_{CE} = 20\text{ V}$ ;  $t_p = 500\text{ }\mu\text{s}$